

# SEMiX191KD16s



**SEMIX® 1s**

## Rectifier Diode Module SEMiX191KD16s

### Features

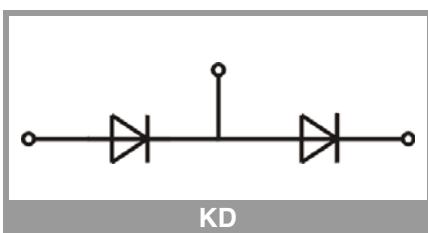
Terminal height 17 mm  
Chips soldered directly to isolated substrate

### Typical Applications\*

- Input Bridge Rectifier for AC/DC motor control
- Power supply

Absolute Maximum Ratings		Values		Unit
Symbol	Conditions			
<b>Rectifier Diode</b>				
$I_{F\text{AV}}$	sin. 180°	$T_c = 85^\circ\text{C}$	190	A
		$T_c = 100^\circ\text{C}$	145	A
$I_{F\text{SM}}$	10 ms	$T_j = 25^\circ\text{C}$	6000	A
		$T_j = 130^\circ\text{C}$	5000	A
$i^2t$	10 ms	$T_j = 25^\circ\text{C}$	180000	$\text{A}^2\text{s}$
		$T_j = 130^\circ\text{C}$	125000	$\text{A}^2\text{s}$
$V_{R\text{SM}}$			1700	V
$V_{R\text{RM}}$			1600	V
$T_j$			-40 ... 130	$^\circ\text{C}$
<b>Module</b>				
$T_{\text{stg}}$			-40 ... 125	$^\circ\text{C}$
$V_{\text{isol}}$	AC sinus 50Hz	1 min	4000	V
		1 s	4800	V

Characteristics		min.	typ.	max.	Unit
Symbol	Conditions				
<b>Diode</b>					
$V_F$	$T_j = 25^\circ\text{C}, I_F = 500 \text{ A}$			1.5	V
$V_{(\text{TO})}$	$T_j = 130^\circ\text{C}$			0.85	V
$r_T$	$T_j = 130^\circ\text{C}$			0.95	$\text{m}\Omega$
$I_{RD}$	$T_j = 130^\circ\text{C}, V_{RD} = V_{RRM}$			12	mA
$R_{\text{th(j-c)}}$		per diode			K/W
					K/W
$R_{\text{th(j-c)}}$	sin. 180	per diode		0.18	K/W
					K/W
<b>Module</b>					
$R_{\text{th(c-s)}}$	per chip				K/W
	per module		0.075		K/W
$M_s$	to heat sink (M5)	3	5		Nm
$M_t$	to terminals (M6)	2.5	5		Nm
$a$				5 * 9,81	$\text{m}/\text{s}^2$
$w$			145		g



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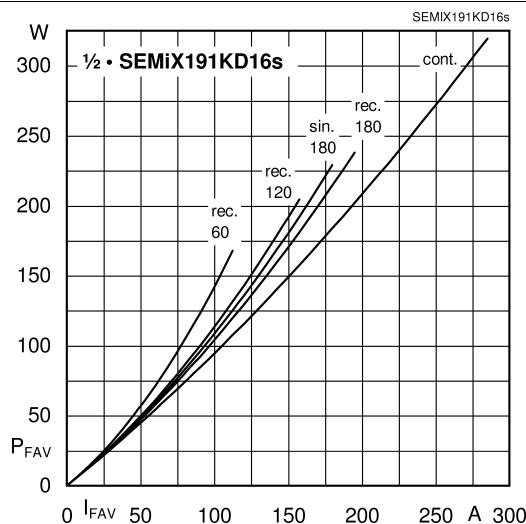


Fig. 1L: Power dissipation per thyristor/diode vs. on-state current

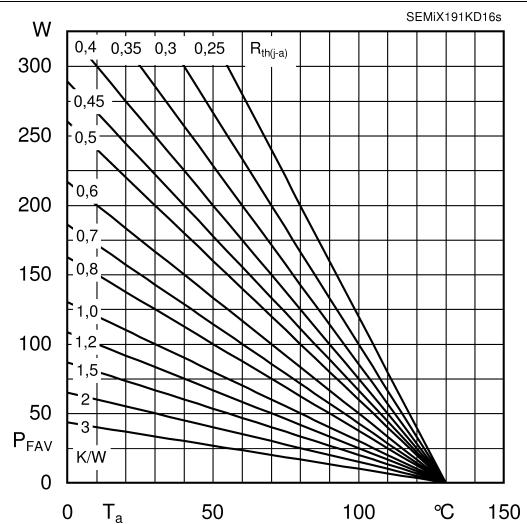


Fig. 1R: Power dissipation per thyristor/diode vs. ambient temperature

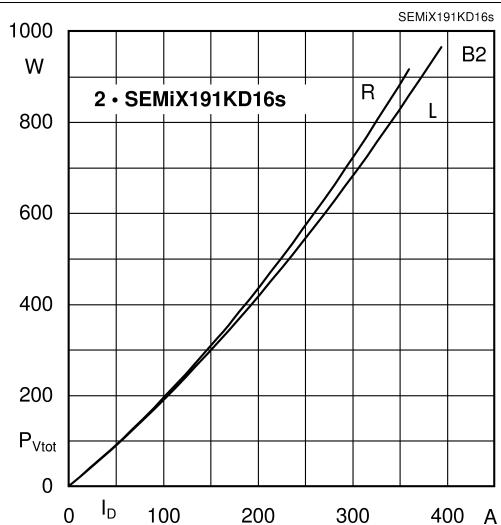


Fig. 3L: Power dissipation of two modules vs. direct current

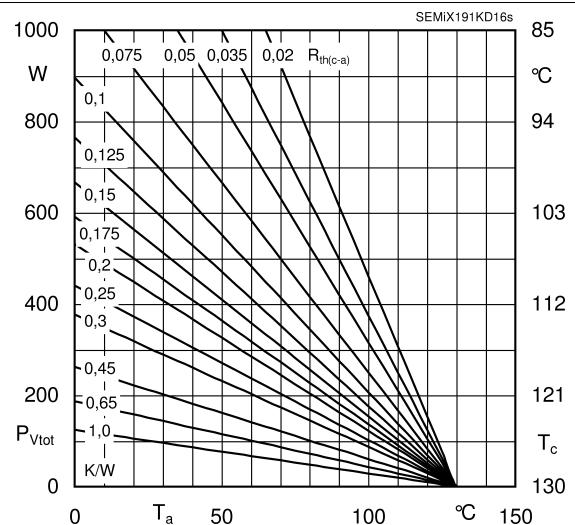


Fig. 3R: Power dissipation of two modules vs. case temperature

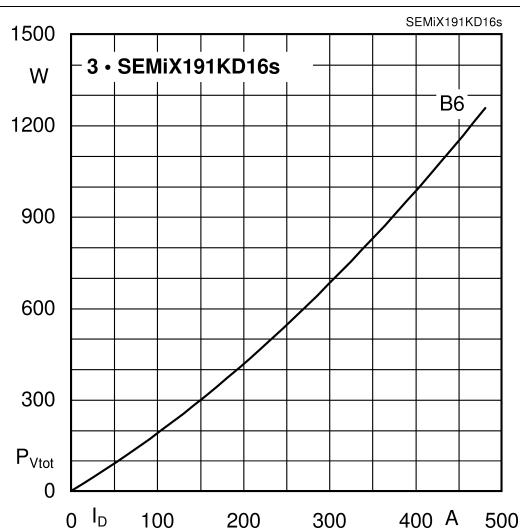


Fig. 4L: Power dissipation of three modules vs. direct current

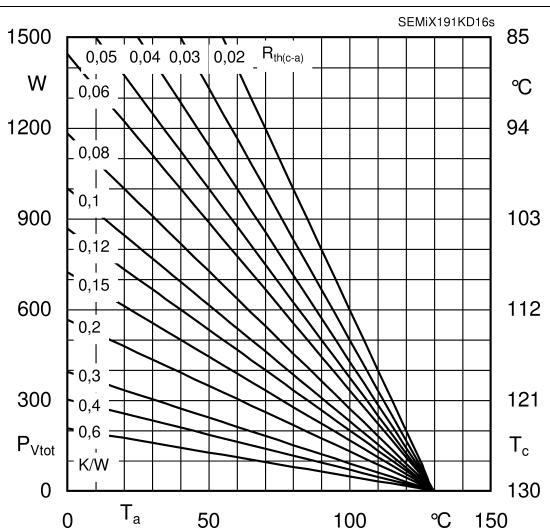


Fig. 4R: Power dissipation of three modules vs. case temperature

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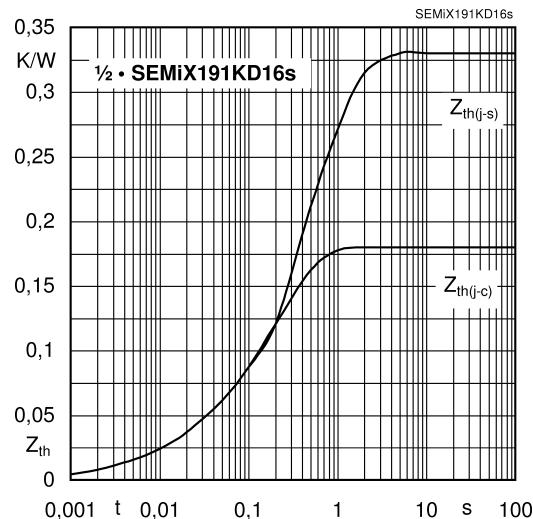


Fig. 6: Transient thermal impedance vs. time

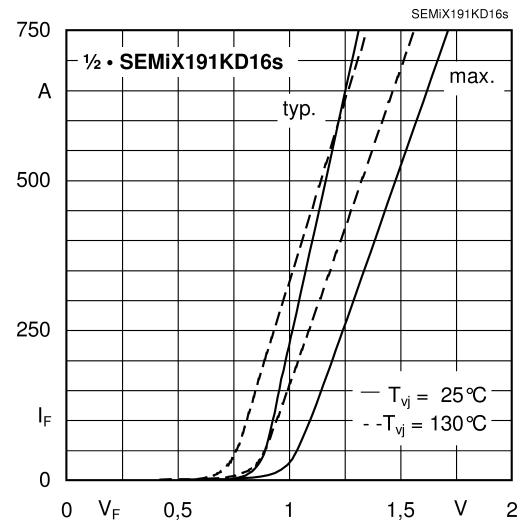


Fig. 7: On-state characteristics

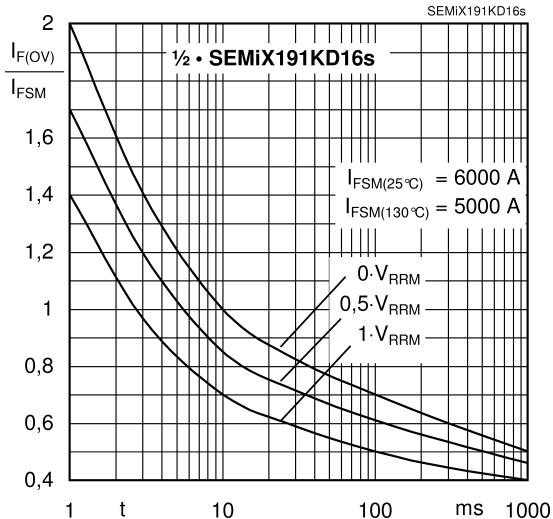
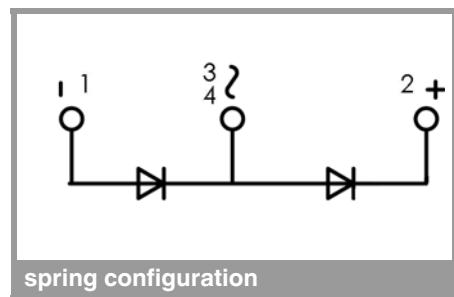
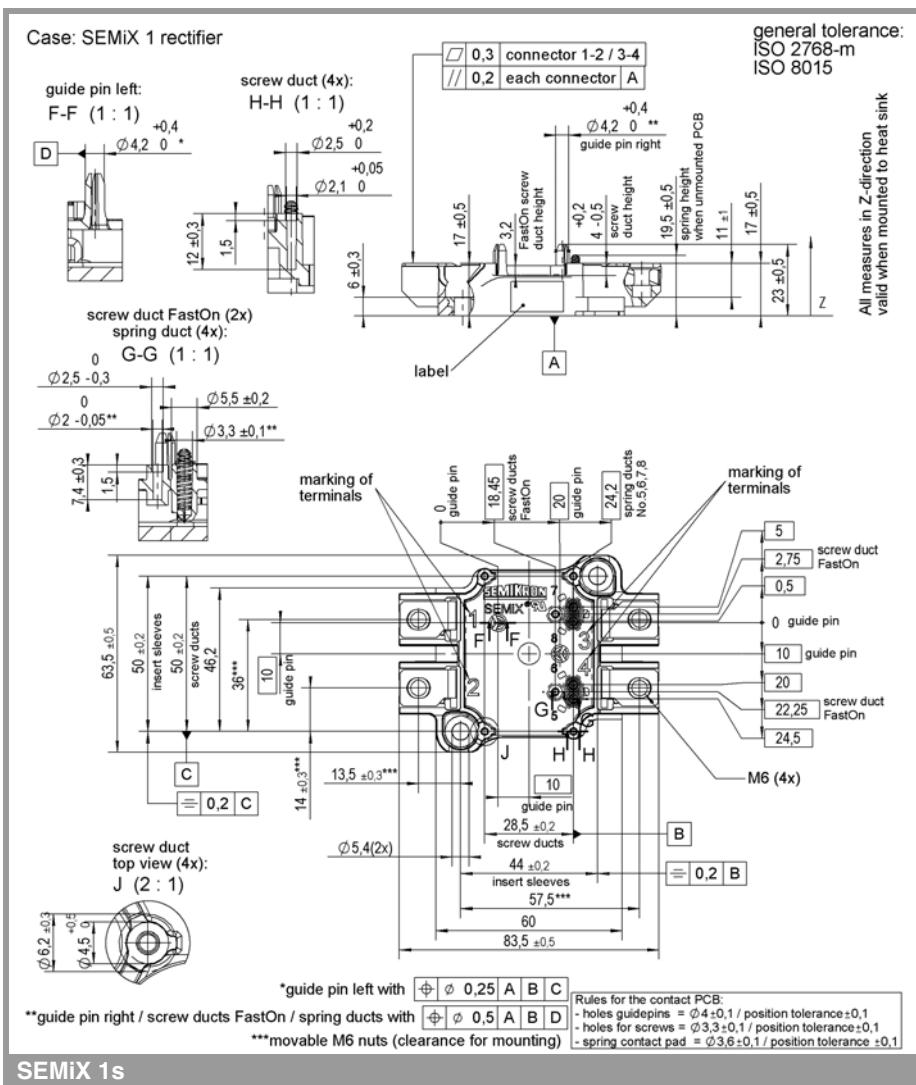


Fig. 8: Surge overload current vs. time

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## SEMiX 1s

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.

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